



## General Description

SFGMOS<sup>®</sup> MOSFET is based on Oriental Semiconductor's unique device design to achieve low  $R_{DS(ON)}$ , low gate charge, fast switching and excellent avalanche characteristics. The high  $V_{th}$  series is specially optimized for high systems with gate driving voltage greater than 10V.

## Features

- Low  $R_{DS(ON)}$  & FOM
- Extremely low switching loss
- Excellent reliability and uniformity
- Fast switching and soft recovery



## Applications

- Switched mode power supply
- Motor driver
- Battery protection
- DC-DC convertor
- Solar inverter
- UPS and energy inverter

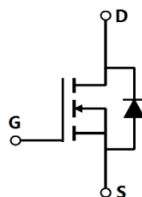
## Key Performance Parameters

| Parameter                         | Value | Unit       |
|-----------------------------------|-------|------------|
| $V_{DS}$                          | 100   | V          |
| $I_D$ , pulse                     | 390   | A          |
| $R_{DS(ON)}$ , max @ $V_{GS}=10V$ | 5     | m $\Omega$ |
| $Q_g$                             | 91.7  | nC         |
| PD                                | 192   | W          |

## Marking Information

| Product Name | Package | Marking   |
|--------------|---------|-----------|
| SFG10R05KF   | TO263   | SFG10R05K |

## Package & Pin information



**Absolute Maximum Ratings** at  $T_j=25^{\circ}\text{C}$  unless otherwise noted

| Parameter                                                                 | Symbol                | Value      | Unit               |
|---------------------------------------------------------------------------|-----------------------|------------|--------------------|
| Drain-source voltage                                                      | $V_{DS}$              | 100        | V                  |
| Gate-source voltage                                                       | $V_{GS}$              | $\pm 20$   | V                  |
| Continuous drain current <sup>1)</sup> , $T_C=25^{\circ}\text{C}$         | $I_D$                 | 130        | A                  |
| Pulsed drain current <sup>2)</sup> , $T_C=25^{\circ}\text{C}$             | $I_{D, \text{pulse}}$ | 390        | A                  |
| Continuous diode forward current <sup>1)</sup> , $T_C=25^{\circ}\text{C}$ | $I_S$                 | 130        | A                  |
| Diode pulsed current <sup>2)</sup> , $T_C=25^{\circ}\text{C}$             | $I_{S, \text{pulse}}$ | 390        | A                  |
| Power dissipation <sup>3)</sup> , $T_C=25^{\circ}\text{C}$                | $P_D$                 | 192        | W                  |
| Single pulsed avalanche energy <sup>5)</sup>                              | $E_{AS}$              | 400        | mJ                 |
| Operation and storage temperature                                         | $T_{stg}, T_j$        | -55 to 150 | $^{\circ}\text{C}$ |

**Thermal Characteristics**

| Parameter                                          | Symbol          | Value | Unit                 |
|----------------------------------------------------|-----------------|-------|----------------------|
| Thermal resistance, junction-case                  | $R_{\theta JC}$ | 0.65  | $^{\circ}\text{C/W}$ |
| Thermal resistance, junction-ambient <sup>4)</sup> | $R_{\theta JA}$ | 62    | $^{\circ}\text{C/W}$ |

**Electrical Characteristics** at  $T_j=25^{\circ}\text{C}$  unless otherwise specified

| Parameter                        | Symbol       | Min. | Typ. | Max. | Unit             | Test condition                                  |
|----------------------------------|--------------|------|------|------|------------------|-------------------------------------------------|
| Drain-source breakdown voltage   | $BV_{DSS}$   | 100  |      |      | V                | $V_{GS}=0\text{ V}, I_D=250\text{ }\mu\text{A}$ |
| Gate threshold voltage           | $V_{GS(th)}$ | 2.0  |      | 4.0  | V                | $V_{DS}=V_{GS}, I_D=250\text{ }\mu\text{A}$     |
| Drain-source on-state resistance | $R_{DS(ON)}$ |      | 4.0  | 5.0  | $\text{m}\Omega$ | $V_{GS}=10\text{ V}, I_D=12\text{ A}$           |
| Gate-source leakage current      | $I_{GSS}$    |      |      | 100  | nA               | $V_{GS}=20\text{ V}$                            |
|                                  |              |      |      | -100 |                  | $V_{GS}=-20\text{ V}$                           |
| Drain-source leakage current     | $I_{DSS}$    |      |      | 1    | $\mu\text{A}$    | $V_{DS}=100\text{ V}, V_{GS}=0\text{ V}$        |

### Dynamic Characteristics

| Parameter                    | Symbol       | Min. | Typ.   | Max. | Unit | Test condition                                                                             |
|------------------------------|--------------|------|--------|------|------|--------------------------------------------------------------------------------------------|
| Input capacitance            | $C_{iss}$    |      | 6388.6 |      | pF   | $V_{GS}=0\text{ V}$ ,<br>$V_{DS}=50\text{ V}$ ,<br>$f=1\text{ MHz}$                        |
| Output capacitance           | $C_{oss}$    |      | 923.3  |      | pF   |                                                                                            |
| Reverse transfer capacitance | $C_{rss}$    |      | 1.4    |      | pF   |                                                                                            |
| Turn-on delay time           | $t_{d(on)}$  |      | 30.9   |      | ns   | $V_{GS}=10\text{ V}$ ,<br>$V_{DS}=50\text{ V}$ ,<br>$R_G=2\ \Omega$ ,<br>$I_D=25\text{ A}$ |
| Rise time                    | $t_r$        |      | 10.0   |      | ns   |                                                                                            |
| Turn-off delay time          | $t_{d(off)}$ |      | 66.8   |      | ns   |                                                                                            |
| Fall time                    | $t_f$        |      | 12.5   |      | ns   |                                                                                            |

### Gate Charge Characteristics

| Parameter            | Symbol        | Min. | Typ. | Max. | Unit | Test condition                                                        |
|----------------------|---------------|------|------|------|------|-----------------------------------------------------------------------|
| Total gate charge    | $Q_g$         |      | 91.7 |      | nC   | $V_{GS}=10\text{ V}$ ,<br>$V_{DS}=50\text{ V}$ ,<br>$I_D=25\text{ A}$ |
| Gate-source charge   | $Q_{gs}$      |      | 23.7 |      | nC   |                                                                       |
| Gate-drain charge    | $Q_{gd}$      |      | 22.3 |      | nC   |                                                                       |
| Gate plateau voltage | $V_{plateau}$ |      | 4.8  |      | V    |                                                                       |

### Body Diode Characteristics

| Parameter                     | Symbol    | Min. | Typ. | Max. | Unit | Test condition                                          |
|-------------------------------|-----------|------|------|------|------|---------------------------------------------------------|
| Diode forward voltage         | $V_{SD}$  |      |      | 1.3  | V    | $I_S=20\text{ A}$ ,<br>$V_{GS}=0\text{ V}$              |
| Reverse recovery time         | $t_{rr}$  |      | 88.0 |      | ns   | $I_S=25\text{ A}$ ,<br>$di/dt=100\text{ A}/\mu\text{s}$ |
| Reverse recovery charge       | $Q_{rr}$  |      | 273  |      | nC   |                                                         |
| Peak reverse recovery current | $I_{rrm}$ |      | 5.2  |      | A    |                                                         |

### Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3)  $P_d$  is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_a=25\text{ }^{\circ}\text{C}$ .
- 5)  $V_{DD}=50\text{ V}$ ,  $V_{GS}=10\text{ V}$ ,  $L=0.3\text{ mH}$ , starting  $T_j=25\text{ }^{\circ}\text{C}$ .

## Electrical Characteristics Diagrams

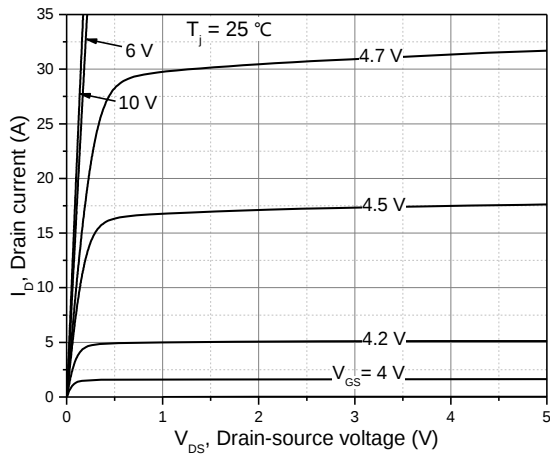


Figure 1. Typ. output characteristics

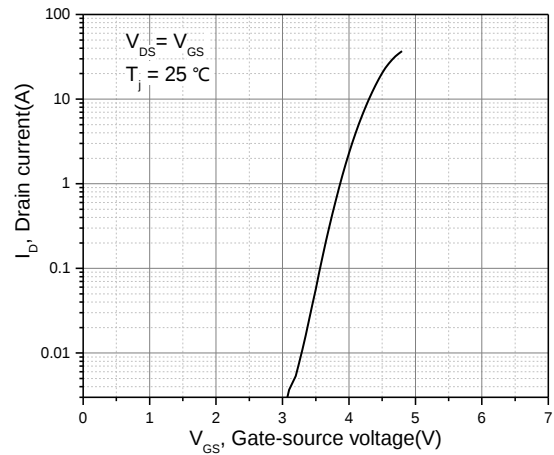


Figure 2. Typ. transfer characteristics

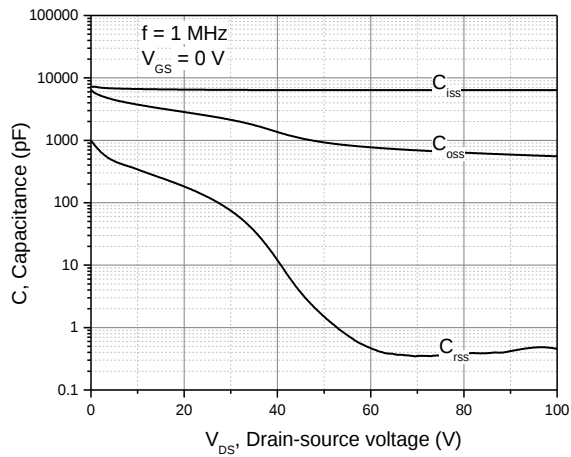


Figure 3. Typ. capacitances

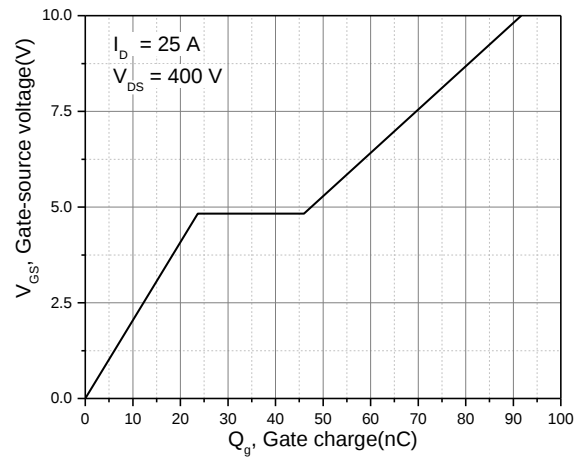


Figure 4. Typ. gate charge

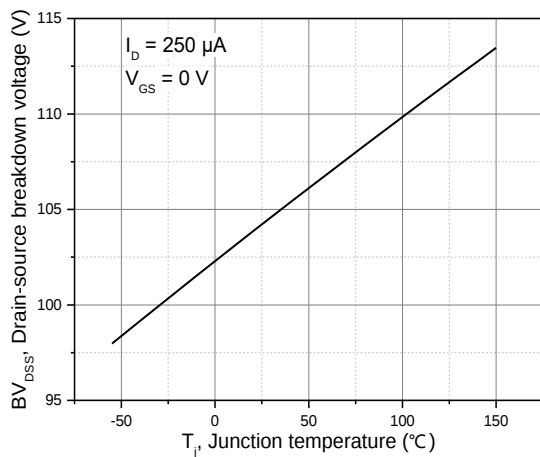


Figure 5. Drain-source breakdown voltage

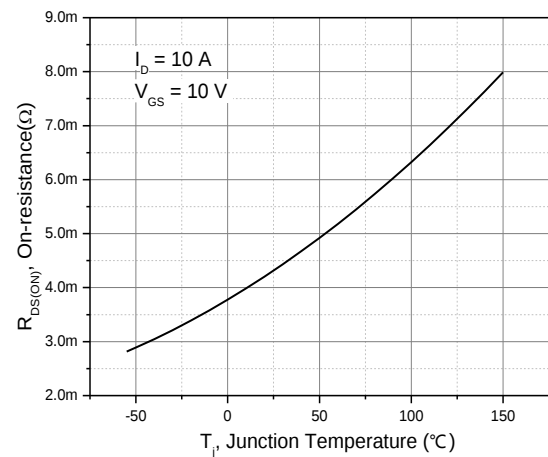
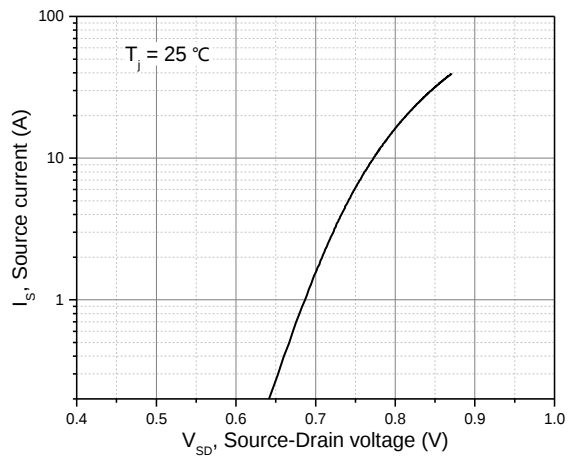
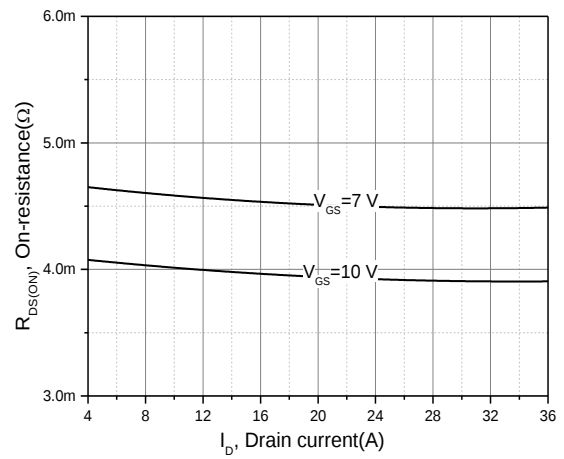


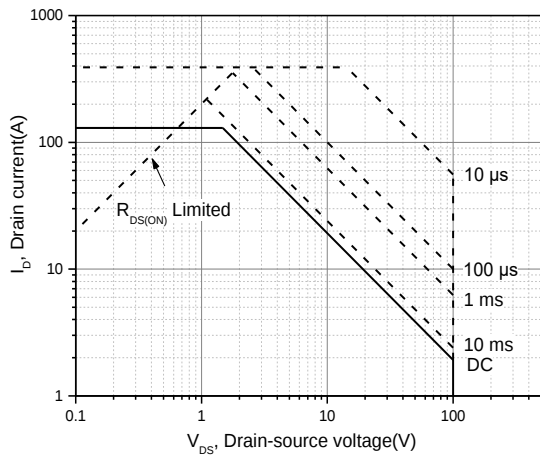
Figure 6. Drain-source on-state resistance



**Figure 7. Forward characteristic of body diode**



**Figure 8. Drain-source on-state resistance**



**Figure 9. Safe operation area  $T_C=25\text{ }^{\circ}\text{C}$**

## Test circuits and waveforms



**Figure 1. Gate charge test circuit & waveform**



**Figure 2. Switching time test circuit & waveforms**

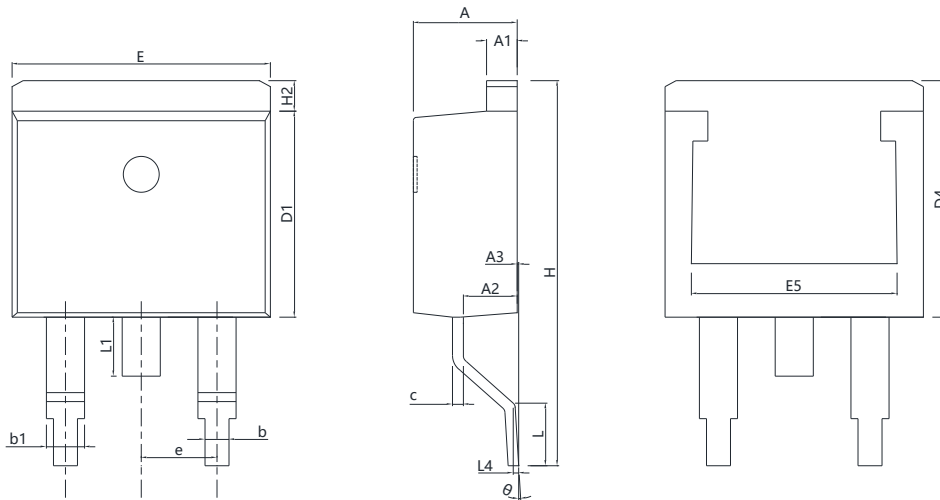


**Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms**



**Figure 4. Diode reverse recovery test circuit & waveforms**

## Package Information



| Symbol | mm       |       |       |
|--------|----------|-------|-------|
|        | Min      | Nom   | Max   |
| A      | 4.37     | 4.57  | 4.77  |
| A1     | 1.22     | 1.27  | 1.42  |
| A2     | 2.49     | 2.69  | 2.89  |
| A3     | 0.00     | 0.13  | 0.25  |
| b      | 0.70     | 0.81  | 0.96  |
| b1     | 1.17     | 1.27  | 1.47  |
| c      | 0.30     | 0.38  | 0.53  |
| D1     | 8.50     | 8.70  | 8.90  |
| D4     | 6.60     | -     | -     |
| E      | 9.86     | 10.16 | 10.36 |
| E5     | 7.06     | -     | -     |
| e      | 2.54 BSC |       |       |
| H      | 14.70    | 15.10 | 15.50 |
| H2     | 1.07     | 1.27  | 1.47  |
| L      | 2.00     | 2.30  | 2.60  |
| L1     | 1.40     | 1.55  | 1.70  |
| L4     | 0.25 BSC |       |       |
| θ      | 0°       | 5°    | 9°    |

Veision 1: TO263-P package outline dimension

## Ordering Information

| Package Type | Units/ Reel | Reels/ Inner Box | Units/ Inner Box | Inner Boxes/ Carton Box | Units/ Carton Box |
|--------------|-------------|------------------|------------------|-------------------------|-------------------|
| TO263-P      | 800         | 1                | 800              | 5                       | 4000              |

## Product Information

| Product    | Package | Pb Free | RoHS | Halogen Free |
|------------|---------|---------|------|--------------|
| SFG10R05KF | TO263   | yes     | yes  | yes          |

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